



Express Mail No.: <u>EV 371 773 148 US</u>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Lee, Wai M. et al.

Confirmation No.: To be assigned

Application No.: 10/694,999

Group Art Unit: To be assigned

Filed: October 29, 2003

Examiner: To be assigned

For:

Apparatus for Substrate Pre-

Treatment

Attorney Docket No.: 60937-226-US

(formerly 8317-226-999)

TRANSMITTAL OF POWER OF ATTORNEY BY ASSIGNEE REVOKING PREVIOUS POWERS OF RECORD

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants' attorney encloses herewith a Revocation and Power of Attorney by Assignee for the above identified application.

<u>Please change the attorney docket number to 60937-226-US</u>. Future correspondence should be forwarded to James S. McDonald, customer no. **24341**.

No fee is believed due at this time, however, the Commissioner is authorized to charge any fees associated with this communication to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310 (Order No. 60937-226-US). A copy of this sheet is enclosed for such purpose.

Respectfully submitted,

Date March 12, 2004

James S. McDonald

(Reg. No. 44,229)

MORGAN, LEWIS & BOCKIUS LLP 3300 Hillview Avenue

Palo Alto, CA 94304

(650) 493-4935



REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, customer no. 24341, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer Number 24341, Morgan, Lewis & Bockius LLP, located at 3300 Hillview Avenue, Palo Alto, California 94304, and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 493-4935.

Assignee:

EKC Technology, Inc.

Date:

7 tel 2004

Signature:

Michael A. Fury

Typed Name: Position/Title:

Vice President, R&D and Engineering

Address:

2520 Barrington Court Hayward, CA 94545



Schedule A

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App #	Title 1	: Inventor(s)	Filing Date	New Attorney Docket No.	Former/Attorney
	Compositions for Cleaning Organic				
l	and Plasma Etched Residues for				
.09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
00/07/000	Method of and Apparatus for				
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
00/005 070	Chemical Mechanical Polishing	0 "	4.410.010.00.4		
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
	Oxalic Acid as a Semiaqueous			•	
10/421 706	Cleaning Product for Copper and Dielectrics	l on otal	04/04/0000	00007 440 110	0047 440 000
10/421,706	Sulfoxide Pyrolid(in)one Alkanolamine	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
10/193,185	Cleaner Composition		07/12/2002	60007 440 110	0047 440 000
10/193,163	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
Ì	Method for the Deposition of Materials				
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	9247 420 000
00/010,044	Post Etch Cleaning Composition for	vasquez, et al.	00/00/2001	00937-120-03	8317-120-999
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123 - US	8317-123-999
10.001,101	Photolytic Conversion Process to	r dyno, ot al.	12/04/2001	00937-120-03	0317-123-999
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
	Cleaning Solutions Including	Diavo vaoquoz, et al.	10/04/2002	00307-120-00	0317-120-999
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation				
09/988,545	Potential	Lee, et al.	.11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for				
	Chemically Treating A Substrate			,	
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
	Cleaning Solution Including				
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation				
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
	Process for the Use of Bis-Choline				
	and Tris-Choline in the Cleaning of				
	Quartz-Coated Polysilicon and Other	·			
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
	Cleaning Compositions Containing				
	Hydroxylamine Derivatives and				
10/055 555	Process Using Same for Residue				
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
	Commontant 5 5 5 % W				
10/690 646	Composition for Exfoliation Agent to	Mark to 14 O	10/00/000	00000	
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
	Reducing Oxide Loss When Using Fluoride Chemistries to Remove Post-				
	Etch Residues in Semiconductor				
60/467,131	Processing	Lee et al	05/02/2002	60027 442 DD	0217 140 000
00/70/,101	i rocessing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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<u> </u>	Tille: 1	se inventor(s) to	Filing Daté	New Attorney Docket No:	Former Attorney Docket No.
	Method for Depositing Patterned				
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
	Methods for the Deposition of Silver				
	and Silver Oxide Films and Patterned				
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
	Semiconductor Process Residue				
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
	System and Method for Cleaning Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Func of al	05/42/2002	C0027 450 DD	0047 450 000
00/409,020	Carboil Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
	Abrasive-Free Chemical Mechanical				
	Polishing Composition and Polishing			,	
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10.000,0.10	, reseas containing carrie	140, 0141.	10/21/2003	00337-131-03	0317-131-333
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
	Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
	Hydrothermal Treatment of				
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
	Chemical Mechanical Polishing	_			
10/401,405	Composition andProcess	Small, et al.	03/27/2003	60937-171-US	8317-171-999
	Aqueous Phosphoric Acid				İ
10/699 000	Compositions for Cleaning	David del	40/04/0000	22227 472 442	
10/688,900	Semiconductor Devices Load Lock System for Supercritical	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
10/465,906	Fluid Cleaning	Eup, et al	06/49/2002	60027 475 116	0247 475 000
10/403,300	Automated Dense Phase Fluid	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Residue Removers for	r dry, or dr.	00/10/2000	00337-170-03	0317-170-333
	Electrohydrodynamic Cleaning of				
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
·	Titanium Carboxylate Films for Use in				
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
	Remover Formulation Containing				
	Fluoride for Use During				
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
1	Cleaning Composition for Removing				
60/464 405	Resists and Manufacturing Method of	1.12			
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
10/422,212	Deposition of Permanent Polymer Structures for OLED Fabrication	Domon et el	04/02/0000	00007 407 110	0047 407 000
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187 - 999

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Арр #	:Titlé		Filing Date	New Attorney Docket No	Former Attorney Docket No.
	Seimconductor Process Residue				
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
	Cleaning Compositions and Method of				
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
	Compositions and Methods for				
•	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
	CMP Method for Copper, Tungsten,				
	Titanium, Polysilicon, and Other				
40/000 000	Substrates Using Organosulfonic		10/20/202		
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
1	PeriodicAcid Compositions for				
60/404 054	Polishing Nobel Metal/High K	Dahad L Carell	00/44/0000	00007 000 00	0047 000 000
60/494,954	Substrates Cerium Oxide Abrasives for Chemical	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60027 204 DD	0247 204 000
00/309,920	Wechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
30/010,100	Periodic Acid Compositions for	Cartor, ot al.	1110-112000	00307-200-110	0317-200-000
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
	Chemical Mechanical Polishing			00001 201 111	
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
	Alumia Abrasive for Chemical				
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing			1	
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				
	Mechanical Planarization of Tantalum				
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
00/500 407	Alumina Abrasive for Chemical		101001000		
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
60/509,922	Particulate or Particle-Bound Chelating Agents	Constitution of all	40/40/0000	C0007 047 DD	0047 047 000
00/309,922	Particulate or Particle-Bound	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	9217 217 000
10/030,020	Chemical Mechanical Polishing of STI		10/23/2003	00937-217-03	8317-217-999
	Features on Semiconductors: Water				
60/533,054	Polishing with Ceria Slurries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
		1 4, 00 41.	12,00,2000	30001 ZZO-1 IX	3017 220-000
	Removal of Post Etch Residues and				
}	Copper Contamination From Low-K				
	Dielectrics Using Superciritcal CO2				
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
	Method and Apparatus for Substrate				, <u></u>
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

'App:#.*	Title :	anventor(s).	Filling Date	New/Attorney Docket/No	Former Attorney Docket No
	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888